



## DOCUMENT CHANGE REQUEST

|            |             |                       |            |               |                            |
|------------|-------------|-----------------------|------------|---------------|----------------------------|
| DCR number | 1637        | Changes required for: | General    | Originator:   | Steve Thacker              |
| Date:      | 2024/03/04  | Date sent:            | 2024/02/05 | Organisation: | ESCC Executive Secretariat |
| Status:    | IMPLEMENTED |                       |            |               |                            |

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| Title: | TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPE STRH8N10 |
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|         |          |        |   |
|---------|----------|--------|---|
| Number: | 5205/023 | Issue: | 9 |
|---------|----------|--------|---|

Other documents affected:

Page:

Various; see attached spec mark-up Draft 10 for details

Paragraph:

See below

Original wording:

As per spec issue 9

Proposed wording:

Amend the maximum limit for Gate-to-Source Threshold Voltage, VGS(th), as follows:  
see attached spec mark-up Draft 10A for details.

Paras. 2.4.1, 2.5, 2.6, 2.10.2:  
to be 4.7V maximum (was 4.5V max.)

Para. 2.4.2:  
for +125C only: to be 4.1V maximum (was 3.7V max.)

Justification:

This DCR is raised on behalf of Manufacturer STM.

STM stated: The reason is: better limit definition due to old and poor statistical data

Attachments:

esc5205023iss10\_draft\_a\_in\_review.docx

Modifications:

N/A

Approval signature:

A handwritten signature in black ink, appearing to be a stylized name or set of initials.

Date signed:

2024-03-04